

	Type	Hits	Search Text	DBs
1	BRS	34	"contact hole" same SAC same ("self aligned" or "self align")	USPAT; EPO; JPO; Derwent; IBM TDB
2	BRS	443	transistor same gate	USPAT; EPO; JPO; Derwent; IBM TDB
3	BRS	54300	"contact hole" or SAC or ("self aligned" or "self align")	USPAT; EPO; JPO; Derwent; IBM TDB
4	BRS	0	("contact hole" same SAC same ("self aligned" or "self align")) same (transistor same gate)	USPAT; EPO; JPO; Derwent; IBM TDB
5	BRS	93133	438/\$.cccls.	USPAT; EPO; JPO; Derwent; IBM TDB
6	BRS	27	438/\$.cccls. and ("contact hole" same SAC same ("self aligned" or "self align"))	USPAT; EPO; JPO; Derwent; IBM TDB
7	BRS	11385	("contact hole" or SAC or ("self aligned" or "self align")) and 438/\$.cccls.	USPAT; EPO; JPO; Derwent; IBM TDB
8	BRS	15392	("contact hole" or SAC or ("self aligned" or "self align")) and "17"	USPAT; EPO; JPO; Derwent; IBM TDB
9	BRS	4	("contact hole" or SAC or ("self aligned" or "self align")) same (transistor same gate)	USPAT; EPO; JPO; Derwent; IBM TDB
10	BRS	40224	("transistor gate" or gate) same length	USPAT; EPO; JPO; Derwent; IBM TDB
11	BRS	15690	("transistor gate" or gate) near6 length	USPAT; EPO; JPO; Derwent; IBM TDB
12	BRS	93269	438/\$.cccls.	USPAT; EPO; JPO; Derwent; IBM TDB
13	BRS	183	((gate near length) same micron) and 438/\$.cccls.	USPAT; EPO; JPO; Derwent; IBM TDB
14	BRS	0	(gate near length) same (micron near .2)	USPAT; EPO; JPO; Derwent; IBM TDB
15	BRS	0	(CHF3 and C2H2F4) same ("silicon oxide")	USPAT; EPO; JPO; Derwent; IBM TDB
16	BRS	57364	C2H2F4 same etching "silicon oxide"	USPAT; EPO; JPO; Derwent; IBM TDB
17	BRS	12880	438/\$.cccls. and (C2H2F4 same etching "silicon oxide")	USPAT; EPO; JPO; Derwent; IBM TDB
18	BRS	57361	C2H2F4 same CHF3 same etching "silicon oxide"	USPAT; EPO; JPO; Derwent; IBM TDB
19	BRS	12880	(C2H2F4 same CHF3 same etching "silicon oxide") and 438/\$.cccls.	USPAT; EPO; JPO; Derwent; IBM TDB
20	BRS	6368	C2H2F4 same CHF3 same etching "silicon oxide" same plasma	USPAT; EPO; JPO; Derwent; IBM TDB

	Time Stamp	Com men ts	Er ror De fin iti on	Er ror s
1	2000/09/11 17:23			0
2	2000/09/11 17:23			0
3	2000/09/11 18:04			0
4	2000/09/11 17:24			0
5	2000/09/11 17:24			0
6	2000/09/11 17:25			0
7	2000/09/11 18:05			0
8	2000/09/11 18:06			0
9	2000/09/11 18:07			0
10	2000/09/12 12:03			0
11	2000/09/12 12:04			0
12	2000/09/12 12:06			0
13	2000/09/19 14:50			0
14	2000/09/12 12:51			0
15	2000/09/12 13:52			0
16	2000/09/12 13:54			0
17	2000/09/12 13:53			0
18	2000/09/12 16:02			0
19	2000/09/12 14:17			0
20	2000/09/12 14:34			0

	Type	Hits	Search Text	DBs
21	BRS	0	(C2H2F4 same CHF3 same etching "silicon oxide" same plasma) same 438/\$.ccls.	USPAT; EPO; JPO; Derwent; IBM TDB
22	BRS	2660	(C2H2F4 same CHF3 same etching "silicon oxide" same plasma) and 438/\$.ccls.	USPAT; EPO; JPO; Derwent; IBM TDB
23	BRS	351	C2H2F4 same CHF3 same etching "silicon oxide" same plasma same (sac or "contact hole")	USPAT; EPO; JPO; Derwent; IBM TDB
24	BRS	202	438/\$.ccls. and (C2H2F4 same CHF3 same etching "silicon oxide" same plasma same (sac or "contact hole"))	USPAT; EPO; JPO; Derwent; IBM TDB
25	BRS	351	"C2H2F4" same "CHF3" same etching "silicon oxide" same plasma same (sac or "contact hole")	USPAT; EPO; JPO; Derwent; IBM TDB
26	BRS	57364	C2H2F4 same etching "silicon oxide"	USPAT; EPO; JPO; Derwent; IBM TDB
27	BRS	12880	(C2H2F4 same etching "silicon oxide") AND 438/\$.ccls.	USPAT; EPO; JPO; Derwent; IBM TDB
28	BRS	354	"C2H2F4" same etching "silicon oxide" same plasma same (sac or "contact hole")	USPAT; EPO; JPO; Derwent; IBM TDB
29	BRS	202	("C2H2F4" same etching "silicon oxide" same plasma same (sac or "contact hole")) AND 438/\$.ccls.	USPAT; EPO; JPO; Derwent; IBM TDB
30	BRS	103	"C2H2F4" same etching "silicon oxide" same plasma same (sac or "contact hole") SAME GATE	USPAT; EPO; JPO; Derwent; IBM TDB
31	BRS	66	("C2H2F4" same etching "silicon oxide" same plasma same (sac or "contact hole") SAME GATE) AND 438/\$.ccls.	USPAT; EPO; JPO; Derwent; IBM TDB
32	BRS	3833	TETRAFLUOROETHANE	USPAT; EPO; JPO; Derwent; IBM TDB
33	BRS	102	TETRAFLUOROETHANE same etching "silicon oxide" same plasma same (sac or "contact hole") SAME GATE	USPAT; EPO; JPO; Derwent; IBM TDB
34	BRS	0	TETRAFLUOROETHANE same etching SAME "silicon oxide" same plasma same (sac or "contact hole") SAME GATE	USPAT; EPO; JPO; Derwent; IBM TDB
35	BRS	3848	TETRAFLUOROETHANE OR C2H2F4	USPAT; EPO; JPO; Derwent; IBM TDB
36	BRS	1	(TETRAFLUOROETHANE OR C2H2F4) same etching same oxide	USPAT; EPO; JPO; Derwent; IBM TDB
37	BRS	425	((TETRAFLUOROETHANE OR C2H2F4) and (CHF3 or trifluoromethane))	USPAT; EPO; JPO; Derwent; IBM TDB
38	BRS	0	((TETRAFLUOROETHANE OR C2H2F4) and (CHF3 or trifluoromethane)) same etching same oxide	USPAT; EPO; JPO; Derwent; IBM TDB

	Time Stamp	Com men ts	Er ror De fin iti on	Er ror s
21	2000/09/12 13:56			0
22	2000/09/12 14:17			0
23	2000/09/12 14:51			0
24	2000/09/12 14:21			0
25	2000/09/12 16:07			0
26	2000/09/12 16:06			0
27	2000/09/12 16:06			0
28	2000/09/12 16:10			0
29	2000/09/12 16:09			0
30	2000/09/12 16:27			0
31	2000/09/12 16:26			0
32	2000/09/12 16:58			0
33	2000/09/12 16:57			0
34	2000/09/12 16:57			0
35	2000/09/12 17:09			0
36	2000/09/19 14:14			0
37	2000/09/12 17:11			0
38	2000/09/12 17:12			0

	Type	Hits	Search Text	DBs
39	BRS	0	((TETRAFLUOROETHANE OR C2H2F4) and (CHF3 or trifluoromethane)) same etching	USPAT; EPO; JPO; Derwent; IBM TDB
40	BRS	479	(gate near length) same micron	USPAT; EPO; JPO; Derwent; IBM TDB
41	BRS	1510	dopant same ("% or "5%")	USPAT; EPO; JPO; Derwent; IBM TDB
42	BRS	93395	438/\$.ccls.	USPAT; EPO; JPO; Derwent; IBM TDB
43	BRS	180	(dopant same ("% or "5%")) and 438/\$.ccls.	USPAT; EPO; JPO; Derwent; IBM TDB

	Time Stamp	Co m m en ts	Er ror De fin iti on	Er ror s
39	2000/09/12 17:12			0
40	2000/09/19 14:53			0
41	2000/09/19 15:48			0
42	2000/09/19 15:48			0
43	2000/09/19 17:28			0